

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. – 5. (Cancelled)

6. (Currently Amended) A writing method of a nonvolatile semiconductor memory device including a plurality of memory cells for storing data of 2 bits in ~~one~~each of said memory cells by setting four threshold voltages for each of the memory cells ~~into four thereof~~, comprising the steps of:

setting the four ~~of the~~ threshold ~~voltage~~voltages by changing them toward a predetermined direction starting from a first threshold voltage and sequentially setting the remaining three of the threshold voltages in order of the remotest threshold voltage from the first threshold voltage, the nearest threshold voltage to the first threshold voltage, and the second remotest threshold voltage from the first threshold voltage.

7. – 10 (Cancelled)

11. (New) A writing apparatus for a nonvolatile semiconductor memory device for storing data of 2 bits in one memory cell by setting threshold voltages of the memory cells into four thereof, comprising:

means for setting the four of the threshold voltage by changing them toward a predetermined direction starting from a first threshold voltage and sequentially

setting the three of the threshold voltages in order of the remotest threshold voltage from the first threshold voltage, the nearest threshold voltage to the first threshold voltage, and the second remotest threshold voltage from the first threshold voltage.

12. (New) A writing apparatus for a nonvolatile semiconductor memory device according to claim 11, wherein

when setting said nearest threshold voltage to the first threshold voltage, said nearest threshold voltage to the first threshold voltage is also set to the memory cell to which the second nearest threshold voltage to the first threshold voltage is set.